To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: http://www.renesas.com

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.
   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.
   The information described here may contain technical inaccuracies or typographical errors.
   Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
   Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).
4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
   Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

HD74UH32

2-input OR Gate

ADE-205-018C (Z)

4th. Edition
Feb. 2003

Description

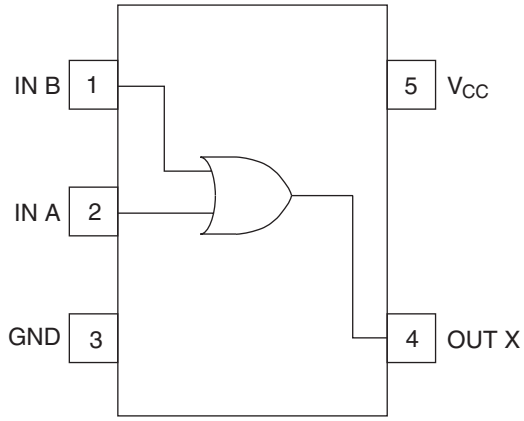
The HD74UH32 is high speed CMOS two input OR gate using silicon gate CMOS process. With CMOS low power dissipation, it provides high speed equivalent to LS-TTL series. The internal circuit of three stages construction with buffer provides wide noise margin and stable output.

Features

- Encapsulated in very small 5pins package of 2.9 × 1.6 × 1.1 mm, the efficiency to mount on substrate is significantly improved.
- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- Electrical characteristics equivalent to the HD74HC32
  Supply voltage range: 2 to 6 V
  Operating temperature range: –40 to +85°C
- $| I_{OH} | = I_{OL}$ = 2 mA (min)
- Ordering Information

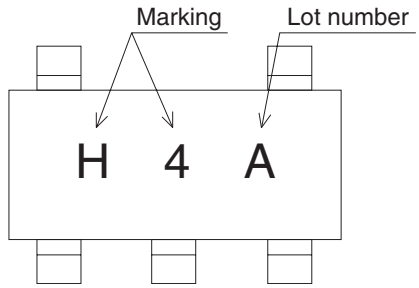
Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD74UH32EL	MPAK-5 pin	MPAK-5V	–	EL (3,000 pcs/reel)

Pin Arrangement



(Top view)

Article Indication



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply voltage	V_{CC}	–0.5 to +7.0	V
Input voltage	V_{IN}	–0.5 to V_{CC} +0.5	V
Output voltage	V_{OUT}	–0.5 to V_{CC} +0.5	V
Input diode current	I_{IK}	±20	mA
Output diode current	I_{OK}	±20	mA
Output current	I_{OUT}	±25	mA
V_{CC}/GND current	I_{CC}, I_{GND}	±25	mA
Power dissipation	P_T	200	mW
Storage temperature	Tstg	–65 to +150	°C

Recommended Operating Conditions

Item	Symbol	Ratings	Unit
Supply voltage	V_{CC}	2 to 6	V
Input voltage	V_{IN}	0 to V_{CC}	V
Output voltage	V_{OUT}	0 to V_{CC}	V
Operating temperature	Topr	–40 to +85	°C
Input rise/fall time	t_r, t_f	0 to 1000 (V_{CC} = 2.0 V)	ns
		0 to 500 (V_{CC} = 4.5 V)	
		0 to 400 (V_{CC} = 6.0 V)	

Electrical Characteristics

			Ta = 25°C			Ta = –40 to 85°C				
Item	Symbol	V_{cc}	Min	Typ	Max	Min	Max	Unit	Test Conditions	
Input voltage	V_{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V_{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V_{OH}	2.0	1.9	2.0	—	1.9	—	V		I_{OH} = –20 µA
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	4.31	—	4.13	—			I_{OH} = –2 mA
		6.0	5.68	5.80	—	5.63	—			I_{OH} = –2.6 mA
	V_{OL}	2.0	—	0.0	0.1	—	0.1	V	V_{IN} = V_{IL}	I_{OL} = 20 µA
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	0.17	0.26	—	0.33			I_{OL} = 2 mA
		6.0	—	0.18	0.26	—	0.33			I_{OL} = 2.6 mA
Input current	I_{IN}	6.0	—	—	±0.1	—	±1.0	µA	V_{IN} = V_{CC} or GND	
Operating current	I_{CC}	6.0	—	—	1.0	—	10.0		V_{IN} = V_{CC} or GND	

Switching Characteristics

(C_L = 15 pF, $t_r = t_f$ = 6 ns, V_{CC} = 5 V)

		Ta = 25°C				
Item	**Symbol**	**Min**	**Typ**	**Max**	**Unit**	**Test Conditions**
Output rise/fall time	t_{TLH}	—	5	10	ns	See Test circuit
	t_{THL}					
Propagation delay time	t_{PLH}	—	7	15	ns	See Test circuit
	t_{PHL}					

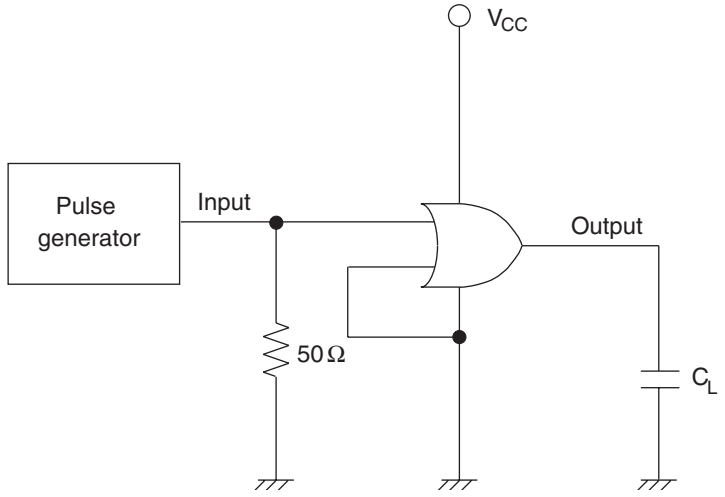
(C_L = 50 pF, $t_r = t_f$ = 6 ns)

			Ta = 25°C			Ta = –40 to 85°C			Test Conditions
Item	**Symbol**	**V_{cc}**	**Min**	**Typ**	**Max**	**Min**	**Max**	**Unit**	
Output rise/fall time	t_{TLH}	2.0	—	50	125	—	155	ns	See Test circuit
	t_{THL}	4.5	—	14	25	—	31		
		6.0	—	12	21	—	26		
Propagation delay time	t_{PLH}	2.0	—	48	100	—	125	ns	See Test circuit
	t_{PHL}	4.5	—	12	20	—	25		
		6.0	—	9	17	—	21		
Input capacitance	C_{IN}	—	—	5	10	—	10	pF	
Equivalent capacitance	C_{PD}	—	—	10	—	—	—		

Note: C_{PD} is equivalent capacitance inside of the IC calculated from the operating current without load (see test circuit). The average operating current without load is calculated according to the expression below.

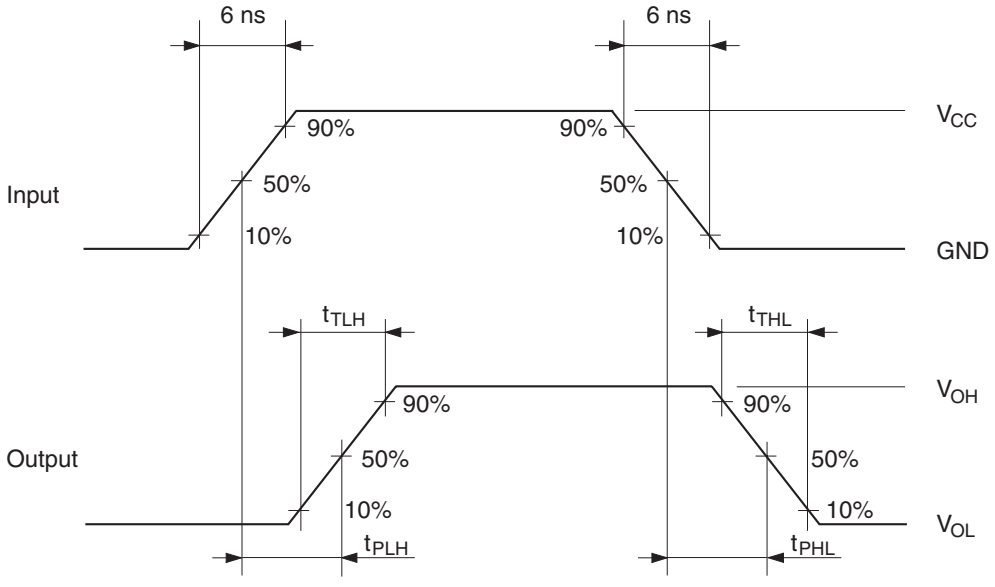
$$I_{CC(opr)} = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$$

Test Circuit



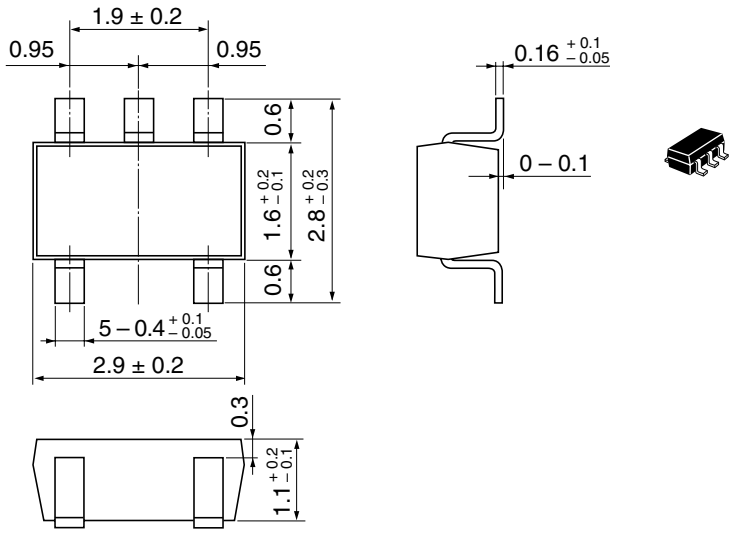
Note: Operating current test time, output is open.

Waveforms



Package Dimensions

Unit: mm



Hitachi Code	MPAK-5V
JEDEC	—
JEITA	—
Mass (reference value)	0.015 g

*Sn-Bi plating

Disclaimer

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

Sales Offices

HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL http://www.hitachisemiconductor.com/

For further information write to:

Hitachi Semiconductor (America) Inc.
179 East Tasman Drive
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe Ltd.
Electronic Components Group
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Europe GmbH
Electronic Components Group
Dornacher Str 3
D-85622 Feldkirchen
Postfach 201, D-85619 Feldkirchen
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel : <65>-6538-6533/6538-8577
Fax : <65>-6538-6933/6538-3877
URL : http://semiconductor.hitachi.com.sg

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel : <886>-(2)-2718-3666
Fax : <886>-(2)-2718-8180
Telex : 23222 HAS-TP
URL : http://semiconductor.hitachi.com.tw

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon Hong Kong
Tel : <852>-2735-9218
Fax : <852>-2730-0281
URL : http://semiconductor.hitachi.com.hk

Colophon 7.0

RENESAS